



SamHop Microelectronics Corp.



SP1087C

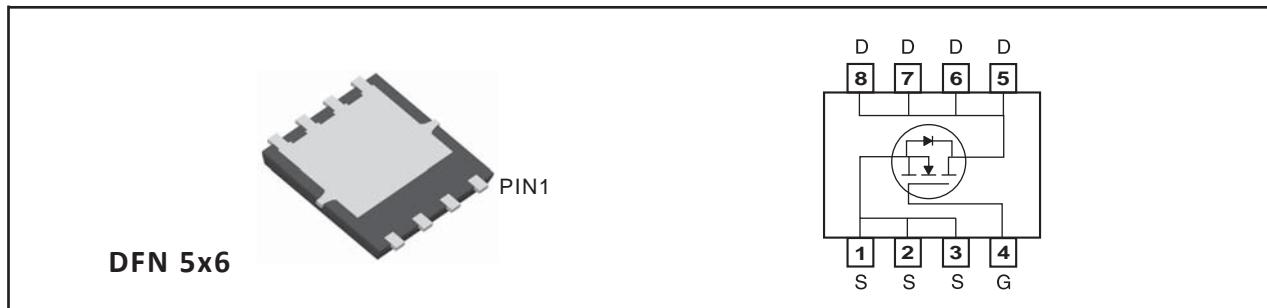
Ver 1.0

## N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
VDSS	ID	RDS(ON) (mΩ) Max
100V	68A	6.9 @ VGS=10V

### FEATURES

- Super high dense cell design for low RDS(ON).
- Rugged and reliable.
- Surface Mount Package.



### ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V <sub>DS</sub>	Drain-Source Voltage		100	V
V <sub>GS</sub>	Gate-Source Voltage		±20	V
I <sub>D</sub>	Drain Current-Continuous <sup>c</sup>	T <sub>C</sub> =25°C	68	A
		T <sub>C</sub> =70°C	54.4	A
I <sub>DM</sub>	-Pulsed <sup>a,c</sup>		138	A
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>d</sup>		812	mJ
P <sub>D</sub>	Maximum Power Dissipation	T <sub>C</sub> =25°C	83	W
		T <sub>C</sub> =70°C	53	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range		-55 to 150	°C

### THERMAL CHARACTERISTICS

R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	1.5	°C/W
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# SP1087C

Ver 1.0

## ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	100			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =80V , V <sub>GS</sub> =0V			1	uA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V , V <sub>DS</sub> =0V			±100	nA
<b>ON CHARACTERISTICS</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	2.7	4	V
R <sub>D(S(ON))</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =10V , I <sub>D</sub> =34A		6.0	6.9	m ohm
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =10V , I <sub>D</sub> =34A		81		S
<b>DYNAMIC CHARACTERISTICS</b> <sup>b</sup>						
C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V f=1.0MHz		3741		pF
C <sub>OSS</sub>	Output Capacitance			500		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			336		pF
<b>SWITCHING CHARACTERISTICS</b> <sup>b</sup>						
t <sub>D(ON)</sub>	Turn-On Delay Time	V <sub>DD</sub> =50V I <sub>D</sub> =1A V <sub>GS</sub> =10V R <sub>GEN</sub> = 6 ohm		67		ns
t <sub>r</sub>	Rise Time			130		ns
t <sub>D(OFF)</sub>	Turn-Off Delay Time			122		ns
t <sub>f</sub>	Fall Time			48		ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =50V, I <sub>D</sub> =25A, V <sub>GS</sub> =10V		58		nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =50V, I <sub>D</sub> =25A, V <sub>GS</sub> =10V		7.6		nC
Q <sub>gd</sub>	Gate-Drain Charge			25		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =17A		0.76	1.3	V
<b>Notes</b>						
a.Pulse Test:Pulse Width < 10us, Duty Cycle < 1%.						
b.Guaranteed by design, not subject to production testing.						
c.Drain current limited by maximum junction temperature.						
d.Starting T <sub>J</sub> =25°C,L=0.5mH,V <sub>DD</sub> = 50V.(See Figure13)						
e.Mounted on FR4 Board of 1 inch <sup>2</sup> , 2oz.						

Nov,20,2015

# SP1087C

Ver 1.0

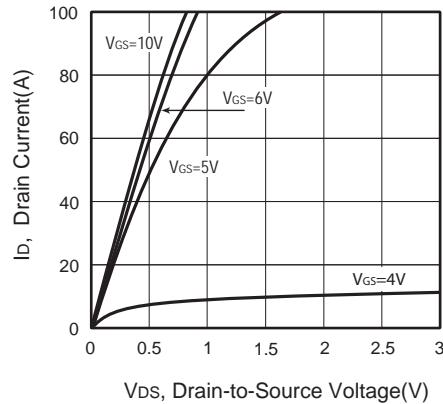


Figure 1. Output Characteristics

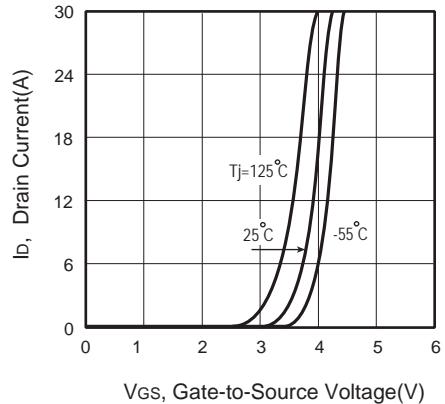


Figure 2. Transfer Characteristics

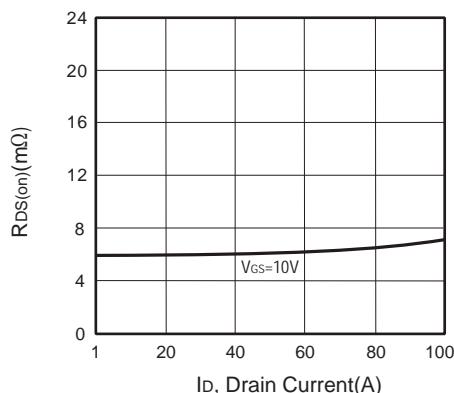


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

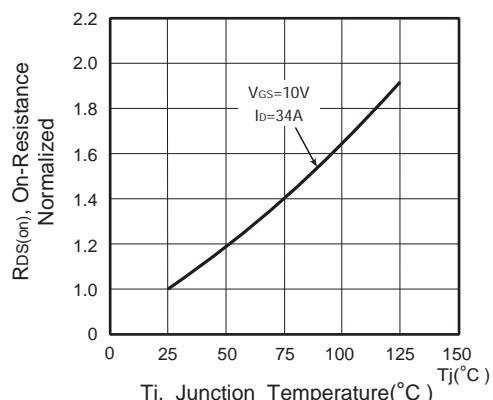


Figure 4. On-Resistance Variation with Drain Current and Temperature

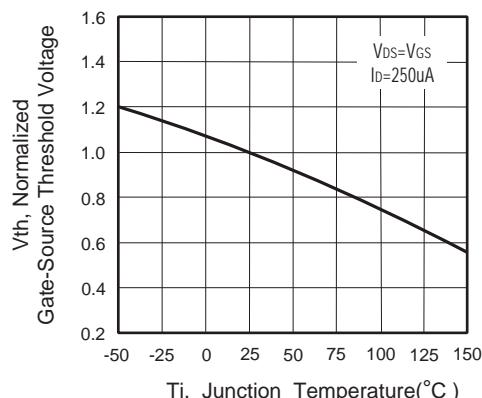


Figure 5. Gate Threshold Variation with Temperature

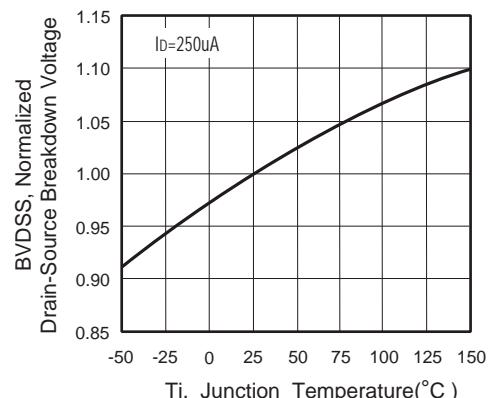


Figure 6. Breakdown Voltage Variation with Temperature

Nov,20,2015

# SP1087C

Ver 1.0

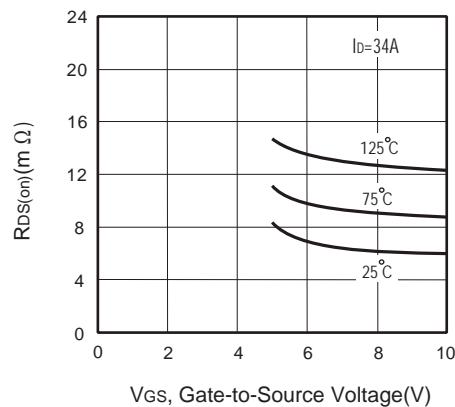


Figure 7. On-Resistance vs. Gate-Source Voltage

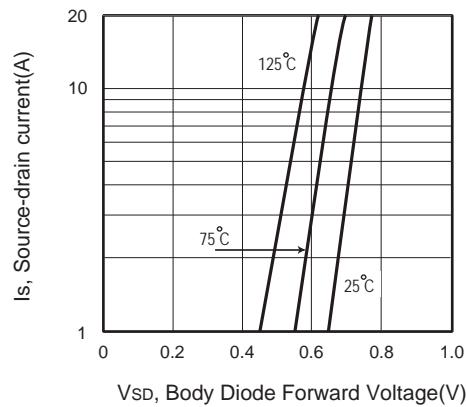


Figure 8. Body Diode Forward Voltage Variation with Source Current

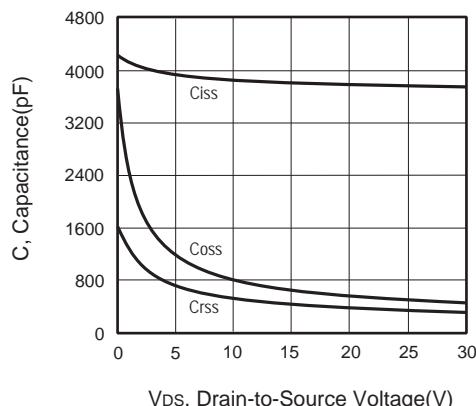


Figure 9. Capacitance

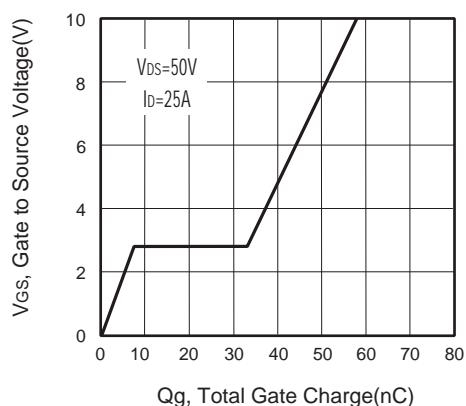


Figure 10. Gate Charge

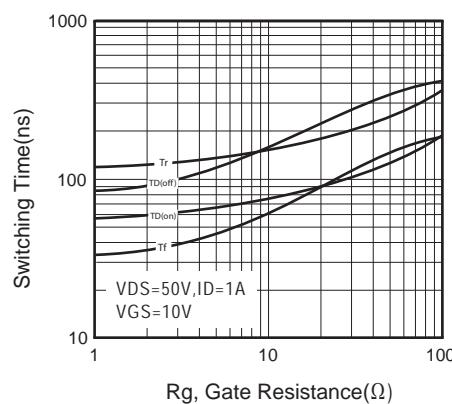


Figure 11. switching characteristics

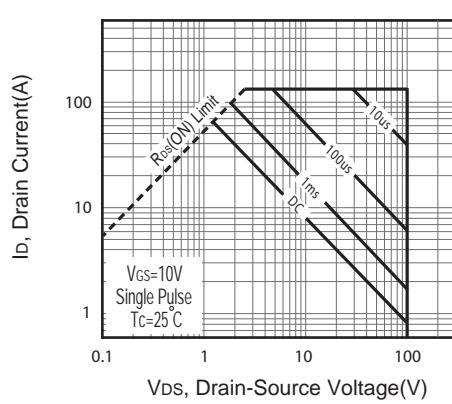
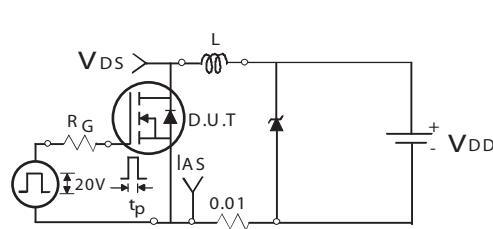


Figure 12. Maximum Safe Operating Area

Nov,20,2015

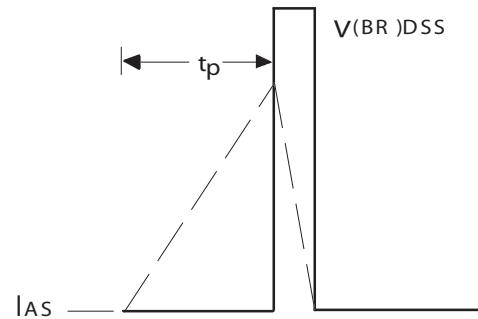
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Ver 1.0



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

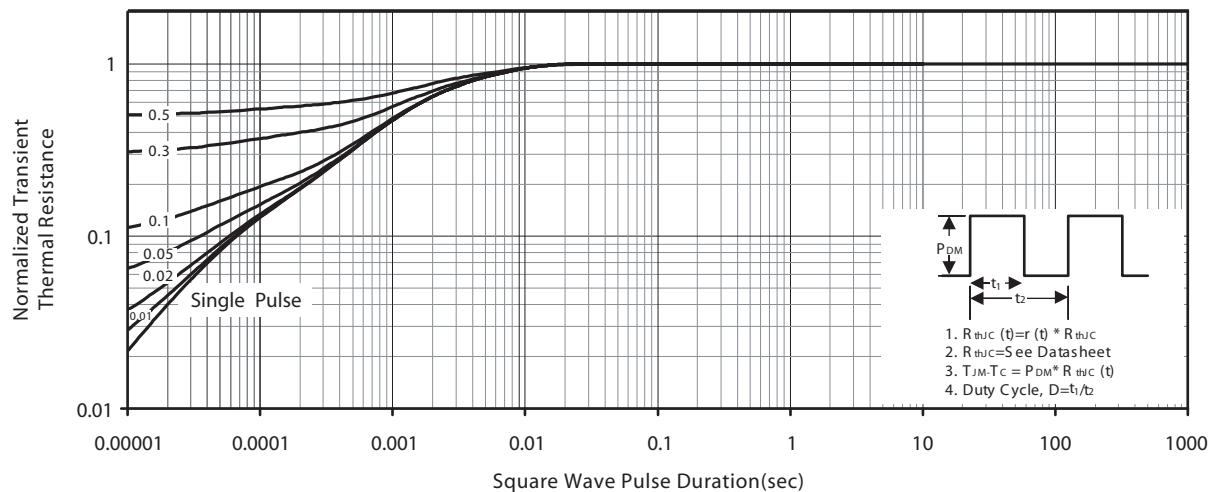
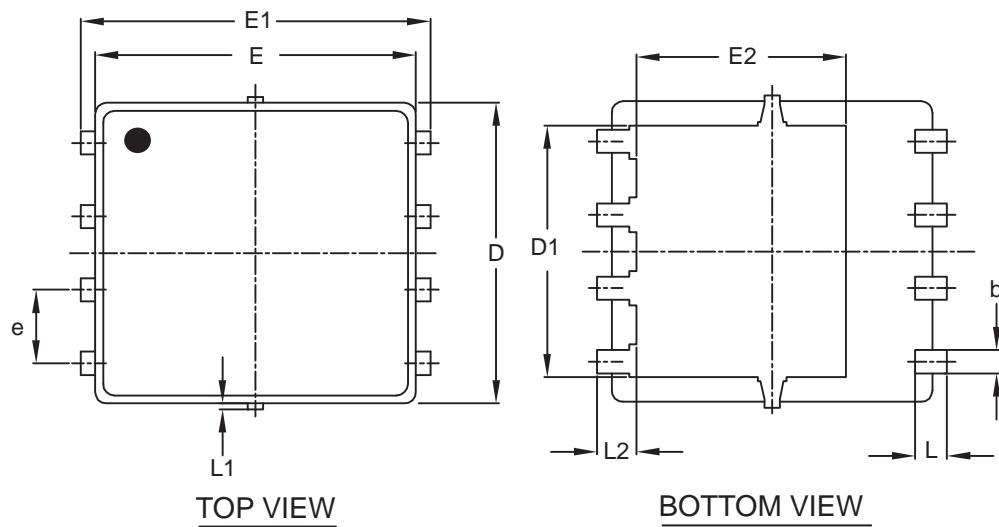


Figure 14. Normalized Thermal Transient Impedance Curve

Nov,20,2015

## PACKAGE OUTLINE DIMENSIONS

**DFN 5x6-8L**



SYMBOLS	MILLIMETERS		
	MIN	NOM	MAX
A	0.85	0.95	1.00
A1	0.00	—	0.05
b	0.30	0.40	0.50
c	0.15	0.20	0.25
D	5.20 BSC		
D1	4.35 BSC		
E	5.55 BSC		
E1	6.05 BSC		
E2	3.62 BSC		
e	1.27 BSC		
L	0.45	0.55	0.65
L1	0.00	—	0.15
L2	0.68 REF		
θ	0°	—	10°

## TOP MARKING DEFINITION

**DFN 5x6-8L**

